

Docket No.: 50432-067

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Kai YANG, et al.

Serial No.: 09/817,056

Filed: March 27, 2001

Group Art Unit: 2811

Examiner: T. NGUYEN

STABILIZING FLUORINE ETCHING OF LOW-K MATERIALS

AMENDMENT

Commissioner for Patents Washington, DC 20231

Sir:

For:

The following Amendment and Remarks are submitted in response to the Office Action dated October 7, 2002.

IN THE CLAIMS:

Please amend claims 1 and 6 as follows.

(Amended) A method of manufacturing a semiconductor device, the 1. method comprising:

forming a single first dielectric layer overlying a substrate;

forming a single mas.

forming a first barrier layer, comprising a first use.

first dielectric layer with an interface therebetween,
etching to form a first opening defined by side surfaces of the first dielectric layer
bottom;

bottom;

bottom; single first dielectric layer with an interface therebetween,

and a bottom;

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